



PATENT
005586/D8326 (81784.0208)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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TECHNOLOGY CENTER 2800

Re application of:

Hidenori OGATA et al.

Serial No: 09/291,538

Filed: April 14, 1999

For: LASER ANNEAL METHOD OF A
SEMICONDUCTOR LAYER

Art Unit: 2822

Examiner: M.A. Wilczewski

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AMENDMENT

Box Non-Fee Amendment
Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to the Office Action dated June 25, 2002, the period for response
to which is being extended to December 25, 2002 by the accompanying Petition,
please amend the above-identified application as follows

[Handwritten signature]
1/7/03

IN THE CLAIMS:

Rewrite claim 9 as follows:

C' 9. (Amended) A transistor device in which a polycrystal semiconductor
layer is formed by subjecting an amorphous semiconductor layer formed on a
substrate to laser anneal processing, wherein
an energy level in a region to be irradiated by a laser beam of the
amorphous semiconductor layer is set such that the level in a rear area of a region
along a scan direction of the laser beam is lower than the upper limit energy level
which maximizes a grain size of the semiconductor layer, and